ABSTRACT

SYSTEM AND METHOD FOR DESIGNING SEMICONDUCTOR PHOTOMASKS

A trial semiconductor photomask design (816) having discontinuity points (302) is provided, and each of the discontinuity points (302) is treated as simulated light sources (202). Simulated light (306) from each of the simulated light sources (302) is focused, and a composite image intensity of the focused simulated light (310) is calculated to verify the trial semiconductor photomask design (816). The trial semiconductor photomask design (816) is sharpened. A photomask design specification (816) is generated for use in fabricating such a photomask (304).

Figure 3